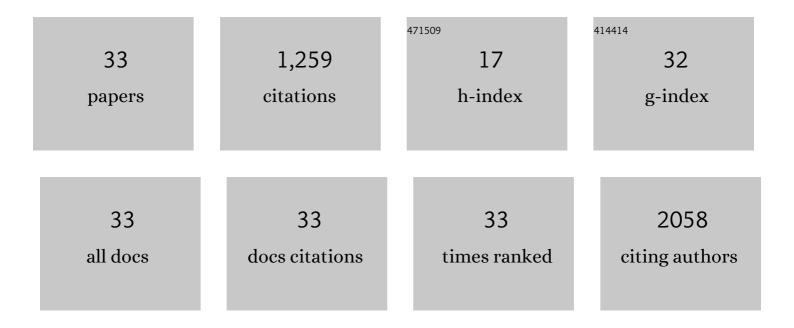
Roger Llopis

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	A two-dimensional spin field-effect switch. Nature Communications, 2016, 7, 13372.	12.8	168
2	Roomâ€Temperature Spin Transport in C ₆₀ â€Based Spin Valves. Advanced Materials, 2011, 23, 1609-1613.	21.0	147
3	A molecular spin-photovoltaic device. Science, 2017, 357, 677-680.	12.6	147
4	A Light ontrolled Resistive Switching Memory. Advanced Materials, 2012, 24, 2496-2500.	21.0	138
5	Active Morphology Control for Concomitant Long Distance Spin Transport and Photoresponse in a Single Organic Device. Advanced Materials, 2016, 28, 2609-2615.	21.0	77
6	Room-temperature air-stable spin transport in bathocuproine-based spin valves. Nature Communications, 2013, 4, .	12.8	74
7	Unveiling the mechanisms of the spin Hall effect in Ta. Physical Review B, 2018, 98, .	3.2	56
8	Resistive switching dependence on atomic layer deposition parameters in HfO ₂ -based memory devices. Journal of Materials Chemistry C, 2014, 2, 3204-3211.	5.5	52
9	Determination of energy level alignment at metal/molecule interfaces by in-device electrical spectroscopy. Nature Communications, 2014, 5, 4161.	12.8	40
10	Energy Level Alignment at Metal/Solutionâ€Processed Organic Semiconductor Interfaces. Advanced Materials, 2017, 29, 1606901.	21.0	37
11	Tuning the resistive switching properties of TiO2â^' <i>x</i> films. Applied Physics Letters, 2015, 106, .	3.3	35
12	Flexible semi-transparent organic spin valve based on bathocuproine. Applied Physics Letters, 2014, 105,	3.3	33
13	Spin doping using transition metal phthalocyanine molecules. Nature Communications, 2016, 7, 13751.	12.8	30
14	Graphene as an electrode for solution-processed electron-transporting organic transistors. Nanoscale, 2017, 9, 10178-10185.	5.6	30
15	C ₆₀ -based hot-electron magnetic tunnel transistor. Applied Physics Letters, 2012, 101, 102404.	3.3	26
16	Tuning the charge flow between Marcus regimes in an organic thin-film device. Nature Communications, 2019, 10, 2089.	12.8	25
17	Roomâ€Temperature Operation of a pâ€Type Molecular Spin Photovoltaic Device on a Transparent Substrate. Advanced Materials, 2020, 32, e1906908.	21.0	20
18	C60/NiFe combination as a promising platform for molecular spintronics. Organic Electronics, 2012, 13, 366-372.	2.6	18

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#	Article	IF	CITATIONS
19	Resistive switching in rectifying interfaces of metal-semiconductor-metal structures. Applied Physics Letters, 2013, 103, .	3.3	15
20	Tailoring palladium nanocontacts by electromigration. Applied Physics Letters, 2013, 102, .	3.3	15
21	Frequency driven inversion of tunnel magnetoimpedance and observation of positive tunnel magnetocapacitance in magnetic tunnel junctions. Applied Physics Letters, 2016, 109, 052401.	3.3	10
22	Non-conventional metallic electrodes for organic field-effect transistors. Organic Electronics, 2012, 13, 2301-2306.	2.6	9
23	One-transistor one-resistor (1T1R) cell for large-area electronics. Applied Physics Letters, 2018, 113, .	3.3	9
24	Reliable determination of the Cu/n-Si Schottky barrier height by using in-device hot-electron spectroscopy. Applied Physics Letters, 2015, 107, .	3.3	8
25	Strain Effects on the Energy-Level Alignment at Metal/Organic Semiconductor Interfaces. ACS Applied Materials & Interfaces, 2019, 11, 12717-12722.	8.0	8
26	In situ electrical characterization of palladium-based single electron transistors made by electromigration technique. AIP Advances, 2014, 4, .	1.3	7
27	Gate-tunable graphene-organic interface barrier for vertical transistor and logic inverter. Applied Physics Letters, 2018, 113, .	3.3	7
28	Three-terminal resistive switching memory in a transparent vertical-configuration device. Applied Physics Letters, 2014, 104, .	3.3	5
29	Top dielectric induced ambipolarity in an n-channel dual-gated organic field effect transistor. Journal of Materials Chemistry C, 2019, 7, 10389-10393.	5.5	5
30	Modulation of spin accumulation by nanoscale confinement using electromigration in a metallic lateral spin valve. Nanotechnology, 2016, 27, 095201.	2.6	3
31	Non-Hebbian Learning Implementation in Light-Controlled Resistive Memory Devices. PLoS ONE, 2012, 7, e52042.	2.5	2
32	Tuning ambipolarity in a polymer field effect transistor using graphene electrodes. Journal of Materials Chemistry C, 2020, 8, 8120-8124.	5.5	2
33	An Artificial Neuron Founded on Resistive Switching of Mott Insulators. , 2017, , .		1